

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	348	semiconductor and dielectric and (hafnium adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/21 11:33
2	BRS	141	(semiconductor and dielectric and (hafnium adj oxide)) and (gate with dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 15:31
3	BRS	1358	257/405,406,410,411.ccls. or 438/216,261,288,591.ccls. (257/405,406,410,411.ccls. or 438/216,261,288,591.ccls.) and ((hafnium adj oxide) or HfO)	USPAT; US-PGPUB	2003/03/21 11:35
4	BRS	29	438/216,261,288,591.ccls.) and ((hafnium adj oxide) or HfO)	USPAT; US-PGPUB	2003/03/21 11:36
5	BRS	26	((257/405,406,410,411.ccls. or 438/216,261,288,591.ccls.) and ((hafnium adj oxide) or HfO)) and (dielectric with (layer or multilayer))	USPAT; US-PGPUB	2003/03/21 11:37